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(54) Title: LASERS WITH LOW DOPED GAIN MEDIUM (57) Abstract A high power, diode pumped laser has an Nd:YVO ₄ gain media. Scaling to higher powers is achieved with the use of a low doped gain media, increasing the length of the gain media as well as increasing the pump volume. Passive cooling is extended to output powers of 10 W or greater.		

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LASERS WITH LOW DOPED GAIN MEDIUM

BACKGROUND OF THE INVENTION

Field of the Invention

5 This invention relates to diode pumped Nd:YVO₄ lasers, and more particularly to diode pumped Nd:YVO₄ lasers with Nd doping levels of less than 0.5%.

Description of Related Art

10 The most common gain media used for diode pumped lasers is Nd:YAG and efficient systems can be constructed by end pumping with laser diodes and laser diode arrays. To build an efficient end pumped Nd:YAG laser, the pump light from the diode, which is typically not in a diffraction limited beam, must be focussed tightly into the gain media. To obtain TEM₀₀ operation, which is desirable for many applications, the pump light must be focussed to a spot size
15 smaller than the intracavity mode. In addition, since the pump light diverges more quickly than the intracavity mode, it must be absorbed in a short distance before it will diverge to a size larger than the intracavity mode. Thus tight focussing and short absorption depths were necessary to build efficient TEM₀₀ Nd:YAG lasers pumped by diode lasers and diode arrays. These techniques are
20 described in U. S. Patents Nos. 4,635,056; 4,701,929; and 4,756,003.

The pump power available from these diode pump sources has increased steadily from 1 W diodes to 20 W diode bars and most recently to 40 W bars at 809 nm. As the pump power increased, several problems were encountered scaling the Nd:YAG lasers to higher power. For the YAG host in particular,
25 increased pump power per unit area leads to increased birefringence. The gain media depolarizes the intra cavity beam; this leads to losses when polarized output is desired. A solution to the birefringence problem is to substitute Nd:YLF as the gain media. YLF is a birefringent material and naturally produces polarized output, even under high thermal loading. YLF, however,
30 suffers from fracture problems as the pump power and hence the thermal

loading is increased. An alternative material which is also naturally polarized and less susceptible to fracture is Nd:YVO₄ (Nd:Vanadate or Vanadate).

As the pump power incident on the Vanadate crystal is increased, thermal lensing becomes the limiting factor. At high pump powers the lens becomes very strong with focal lengths as short as 10 cm. Although this strong lens can be largely compensated by clever cavity design, the aberrations in the lens eventually degrade the performance of the laser. Thus, in order to take advantage of the new higher power diode bars as pump sources, a solution to the aberrated thermal lens in Vanadate is needed.

The power of the lens in a diode pumped Vanadate laser is due to two major contributions: the lens due to the index change in the bulk and the lens due to the bulge in the surface of the crystal. One solution to reducing the surface bulge is to optically contact undoped Vanadate on the end of the gain media. These end caps do not reduce the lens in the bulk however, which is the subject of the following disclosure. Another technique to reduce the surface bulge is to pass the pump light through the crystal more than once. For example, a highly reflective coating for the pump light can be placed on the second surface of the crystal. The pump light will then pass twice through the crystal causing the pump to be absorbed more homogeneously throughout the crystal and causing less heating near the surface. Either of these techniques may be used in combination with the method described below to reduce the thermal lens even further.

There is a need for a Vanadate laser or laser system with higher powers. There is also a need for a Vanadate laser or laser system with a reduced lens in the bulk of the crystal.

SUMMARY OF THE INVENTION

Accordingly, an object of the invention is to provide a diode-pumped Nd:YVO₄ laser.

Another object of the invention is to provide a diode-pumped Nd:YVO₄ laser that is scalable to high power.

Yet another object of the invention is to provide a high power diode-pumped Nd:YVO₄ laser with a TEM₀₀ beam with high efficiency.

A further object of the invention is to provide a compact diode-pumped Nd:YVO₄ laser.

5 Yet another object of the invention is to provide a diode-pumped Nd:YVO₄ laser that is passively cooled.

These and other objects of the invention are achieved in a diode pumped laser with a first high reflector mirror and an output coupler that defines a resonator cavity. A first Nd:YVO₄ gain medium is positioned in the resonator
10 cavity. The gain medium has an Nd doping level of less than 0.5% and a length of at least 4 mm. A first diode pump source supplies a first pump beam that is incident on a first pump face of the first Nd:YVO₄ gain medium.

In another embodiment of the invention, a diode pumped laser has a first high reflector mirror and an output coupler that defines a resonator cavity. A
15 first Nd:YVO₄ gain medium is positioned in the resonator cavity with a pump volume of at least 8 mm³. A first diode pump source supplies a first pump beam that end pumps a first pump face of the first Nd:YVO₄ gain medium.

In another embodiment of the invention, a diode pumped laser includes a first high reflector mirror and an output coupler that define a resonator cavity.
20 A first Nd:YVO₄ gain medium is positioned in the resonator cavity. The Nd:YVO₄ gain medium has a length greater than 8 mm. A first diode pump source supplies a first pump beam that is incident on a first pump face of the first Nd:YVO₄ gain medium.

In another embodiment of the invention, a diode pumped laser includes a
25 first high reflector mirror and an output coupler that define a resonator cavity. A first Nd:YVO₄ gain medium is positioned in the resonator cavity. The first Nd:YVO₄ gain medium has a doping level and a pump volume that permit the first Nd:YVO₄ gain medium to be passively cooled. A first diode pump source supplies a first pump beam that is incident on a first pump face of the first
30 Nd:YVO₄ gain medium. The laser produces an output beam with a power of at least 5 watts at 532 nm.

In another embodiment of the invention, a diode pumped laser includes a first high reflector mirror and an output coupler that define a resonator cavity. A first Nd:YVO₄ gain medium is positioned in the resonator cavity. The first Nd:YVO₄ gain medium has a doping level and a pump volume selected to permit the first Nd:YVO₄ gain medium to be passively cooled. A first diode pump source supplies a first pump beam that is incident on a first pump face of the first Nd:YVO₄ gain medium. The laser produces an output beam with a power of at least 10 watts at 1064 nm.

BRIEF DESCRIPTION OF THE FIGURES

Figure 1 is a schematic diagram of a laser of the present invention with a single Nd:YVO₄ gain medium pumped by a first diode pump source.

Figure 2 is a schematic diagram of a laser of the present invention with a single Nd:YVO₄ gain medium pumped by a two diode pump sources.

Figure 3 is a schematic diagram of a laser of the present invention with a first Nd:YVO₄ gain medium pumped by first and second diode pump sources, and a second Nd:YVO₄ gain medium pumped by third and fourth diode pump sources.

Figure 4 is a schematic diagram of a laser of the present invention with two shorter Nd:YVO₄ crystals that effectively act as a single crystal; illustrated is an aperture positioned between the two crystals.

DETAILED DESCRIPTION

Referring now to Figure 1, a diode pumped laser 10 has a resonator cavity 12 defined by a first high reflector mirror 14 and an output coupler 15 that defines a resonator cavity. A first Nd:YVO₄ gain medium 16 is positioned in the resonator cavity. A first diode pump source 18 supplies a first pump beam 20 that is incident on a first pump face 22 of first Nd:YVO₄ gain medium 16. Optionally, a back surface 30 of first Nd:YVO₄ gain medium 16 can be coated with a coating that is reflective for pump light from first pump beam 20.

First diode pump source 18 can be a single emitter, a broad stripe emitter or a diode bar. First diode pump source 18 can be associated with one or more lenses 24 in order to focus first pump beam 20 from first diode source 18 so that it is incident on gain medium 16. In one embodiment, two lenses are provided in a telescope arrangement to optimize the size of the pump beam. First diode pump source 18 can be fiber coupled. In one specific embodiment, first diode pump source 18 provides a first pump beam 20 with at least 20 watts of power incident on first pump face 22 of first Nd:YVO₄ gain medium 16.

In various embodiments, laser 10 has high efficiency with at least 35% of the pump power being converted to output power. In one embodiment, the pump power at 809 nm is converted efficiently to an output at 1064 nm with a TEM₀₀ output beam. Laser 10 can be a high power laser that produces at least 10 watts at 1064 nm.

Referring now to Figure 2, laser 10 includes a second diode pump source 26 supplying a second pump beam 28 that is incident on a second pump face 30 of first Nd:YVO₄ gain medium 16. Second diode pump source 26 can be associated with one or more lenses 32 similar to lenses 24.

The embodiment illustrated in Figure 2 is a Z fold geometry that includes fold mirrors 34 and 36 which can be highly reflective at 1064 nm and highly transmissive at 809 nm.

Another embodiment of laser 10 is illustrated in Figure 3 that includes first and second Nd:YVO₄ gain media with four diode pump sources. A third diode pump source 38 produces a third pump beam 40 that is incident on first pump face 41 of second Nd:YVO₄ gain medium 43. A fourth diode pump source 42 produces a fourth pump beam 44 incident on a second pump face 46 of second Nd:YVO₄ gain medium 43. Optionally included are one or more telescopic lens arrangements 48 and 50. In all embodiments illustrated in Figures 1-4, laser 10 produces an output beam 52.

In various embodiments, first and second Nd:YVO₄ gain medium 16 and 43 can have Nd doping levels of less than 0.5%, 0.4%, 0.3%, 0.2% and 0.1%.

First and second Nd:YVO₄ gain medium 16 and 43 can have pump volumes of at least 8 mm³, 10 mm³ or 12 mm³.

5 The effective absorption length of Nd:YVO₄ gain medium 16 depends primarily on 3 parameters: the crystal doping, the pump wavelength and the crystal length. To increase the absorption depth beyond the typical value of 4 to 8 mm, first a longer crystal can be used. A combination of lower doping and detuning of the pump wavelength away from the peak of the absorption can be used so that the pump power is distributed throughout the entire crystal. This can also be achieved by broadening the pump bandwidth around the peak of the absorption. The "pump volume" is defined as the volume in which the gain media is excited by the pump. Typically, the pump volume is shaped like a cylinder with a diameter determined by the diameter of the pump light and a length determined by the crystal length.

15 Typical Vanadate systems use a pump diameter of 0.7 mm and a crystal length of 4 or 8 mm. Thus the pump volume would be 1.5 or 3 mm³ respectively. With a Nd doping of 1% in a 4 mm crystal or 0.5% in an 8 mm crystal, approximately 90 % of the pump light is absorbed. When greater than 13 W of pump light at the peak absorption wavelength for Nd:Vanadate (809 nm) is incident on one face of the crystal, the thermal lens becomes sufficiently aberrated to reduce the laser efficiency.

20 In one embodiment of the invention, the thermal lens is reduced by increasing the pump mode to 1.1 mm, increasing the crystal length to 12 mm and reducing the Nd doping to 0.27%. In this case the pump volume is increased to 12 mm³. Pump powers up to 26 W on one face have been used without reduced laser efficiency. For high power systems, this crystal configuration can be used with 26 W of pump power on each of the two faces of the crystal.

25 First and second Nd:YVO₄ gain medium 16 and 43 can have lengths greater than 8 mm, 10 mm, 12 mm or 16 mm. The lengths of first and second Nd:YVO₄ can be achieved with a single crystal or by positioning two crystals 30 16' and 16" (Figure 4) in close proximity to each other or in a contacting

relationship. Crystals 16' and 16" are positioned sufficiently close to each other to act as a single crystal. It will be appreciated that one of both of the two crystals can be coated, or an intracavity element, including but not limited to an aperture 54, can be positioned between crystals 16' and 16".

5 Low power diode pumped solid state lasers can be "passively cooled". For purposes of this disclosure passive cooling is achieved by conducting the heat away using metal components in intimate contact with the gain media. These metal components may also be attached to fins or heat spreading plates. Prior to this invention, as the pump power was increased, "active cooling"

10 methods become necessary to keep the laser from having extended warm-up times or fluctuating performance as the ambient temperature was varied. Active cooling methods included: water cooled heat sinks, TE coolers and fans. With the present invention, reducing the thermal lens in a Vanadate laser permits the use of passive cooling to obtain high performance at higher pump powers and

15 hence higher output powers. Vanadate lasers can now be operated at 10 W average power or frequency doubled to 5 W average power in the green with only passive cooling.

 In various embodiments, laser 10 is compact. Compactness is achieved by passive cooling and/or the use of fiber-coupled diode bars as the pump

20 source. Compactness is also achieved with the use of fiber-coupled diode bars. By placing the diode bars in the power supply, cooling of the diode source is eliminated from the laser head. Compactness provides greater thermal and mechanically stability of laser 10.

 First, second, third and fourth diode pump sources 18, 26, 38 and 42 can

25 be fiber coupled. Preferably, laser 10 is end-pumped by first, second, third and fourth diode pump sources 18, 26, 38 and 42. In one embodiment, first, second, third and fourth diode pump sources 18, 26, 38 and 42 can produce at least 20 watts of power incident upon their respective pump faces of first and second Nd:YVO₄ gain medium 16 and 43 respectively. In the different embodiments

30 of Figures 1-3, output beam 52 can have a power of at least 5 watts, 7 watts and

10 watts at 532 nm. Output beam 52 can have a power of at least 10 watts, 15 watts and 20 watts at 1064 nm.

5 The foregoing description of a preferred embodiment of the invention has been presented for purposes of illustration and description. It is not intended to be exhaustive or to limit the invention to the precise forms disclosed. Obviously, many modifications and variations will be apparent to practitioners skilled in this art. It is intended that the scope of the invention be defined by the following claims and their equivalents.

What is claimed is:

CLAIMS

- 1 1. A diode pumped laser, comprising:
2 a first high reflector mirror and an output coupler defining a
3 resonator cavity;
4 a first Nd:YVO₄ gain medium positioned in the resonator cavity, the
5 gain medium having a doping level of less than 0.5% and a length of at least
6 4 mm; and
7 a first diode pump source supplying a first pump beam that is
8 incident on a first pump face of the first Nd:YVO₄ gain medium.
- 1 2. The laser of claim 1, wherein the doping level is no greater
2 than 0.4%.
- 1 3. The laser of claim 1, wherein the doping level is no greater
2 than 0.3%.
- 1 4. The laser of claim 1, wherein the doping level is no greater
2 than 0.2%.
- 1 5. The laser of claim 1, wherein the doping level is no greater
2 than 0.1%.
- 1 6. The laser of claim 1, wherein the doping level is 0.27%.
- 1 7. The laser of claim 1, wherein a length of the first Nd:YVO₄
2 gain medium is at least 8 mm.

1 8. The laser of claim 1, wherein the first Nd:YVO₄ gain
2 medium is end-pumped by the first pump beam.

1 9. The laser of claim 1, wherein the first Nd:YVO₄ gain
2 medium has a pump volume of at least 8 mm³.

1 10. The laser of claim 1, wherein the first Nd:YVO₄ gain
2 medium has a pump volume of at least 10 mm³.

1 11. The laser of claim 1, wherein the first diode pump source is a
2 fiber coupled diode pump source.

1 12. The laser of claim 11, wherein the first diode pump source
2 provides a pump beam with at least 20 watts of power incident on the first
3 pump face of the first Nd:YVO₄ gain medium.

1 13. The laser of claim 1, further comprising:

1 a second diode pump source supplying a second pump beam that is
2 incident on a second pump face of the first Nd:YVO₄ gain medium.

1 14. The laser of claim 13, wherein the first and second diode
2 pump sources are fiber coupled.

1 15. The laser of claim 14, wherein the second diode pump source
2 provides a pump beam with at least 20 watts of power incident on the
3 second pump face of the first Nd:YVO₄ gain medium.

1 16. The laser of claim 13, further comprising:
2 a second Nd:YVO₄ gain medium positioned in the resonator cavity;
3 a third diode pump source supplying a third pump beam that is
4 incident on a first pump face of the second Nd:YVO₄ gain medium; and
5 a fourth diode pump source supplying a fourth pump beam that is
6 incident on a second pump face of the second Nd:YVO₄ gain medium.

1 17. The laser of claim 16, wherein the first, second, third and
2 fourth diode pump sources are fiber coupled diode pump sources.

1 18. The laser of claim 1, wherein the laser produces an output
2 beam with a power of at least 10 watts at 532 nm.

1 19. The laser of claim 1, wherein the laser produces an output
2 beam with a power of at least 20 watts at 1064 nm.

1 20. A diode pumped laser, comprising:
2 a first high reflector mirror and an output coupler defining a
3 resonator cavity;
4 a first Nd:YVO₄ gain medium positioned in the resonator cavity
5 with a pump volume of at least 8 mm³; and
6 a first diode pump source supplying a first pump beam that end
7 pumps a first pump face of the first Nd:YVO₄ gain medium.

1 21. The laser of claim 20, wherein the pump volume is at least
2 10 mm³.

1 22. The laser of claim 20, wherein the pump volume is at least
2 12 mm³.

1 23. The laser of claim 20, wherein a doping level of the first
2 Nd:YVO₄ gain medium is less than 0.5%.

1 24. The laser of claim 20, wherein a length of the first Nd:YVO₄
2 gain medium is greater than 8 mm.

1 25. The laser of claim 20, wherein the first diode pump source is
2 fiber coupled.

1 26. The laser of claim 25, wherein the first diode pump source
2 provides a pump beam with at least 20 watts of power incident on the first
3 pump face of the first Nd:YVO₄ gain medium.

1 27. The laser of claim 20, further comprising:

1 a second diode pump source supplying a second pump beam that is
2 incident on a second pump face of the first Nd:YVO₄ gain medium.

1 28. The laser of claim 27, wherein the first and second diode
2 pump sources are fiber coupled.

1 29. The laser of claim 28, wherein the second diode pump source
2 provides a pump beam with at least 20 watts of power incident on the
3 second pump face of the first Nd:YVO₄ gain medium.

1 30. The laser of claim 27, further comprising:
2 a second Nd:YVO₄ gain medium positioned in the resonator cavity;
3 a third diode pump source supplying a third pump beam that is
4 incident on a first pump face of the second Nd:YVO₄ gain medium; and
5 a fourth diode pump source supplying a fourth pump beam that is
6 incident on a second pump face of the second Nd:YVO₄ gain medium.

1 31. The laser of claim 30, wherein the first, second, third and
2 fourth diode pump sources are fiber coupled.

1 32. The laser of claim 20, wherein the laser produces an output
2 beam with a power of at least 10 watts at 532 nm.

1 33. The laser of claim 20, wherein the laser produces an output
2 beam with a power of at least 20 watts at 1064 nm.

1 34. A diode pumped laser, comprising:
2 a first high reflector mirror and an output coupler defining a
3 resonator cavity;
4 a first Nd:YVO₄ gain medium positioned in the resonator cavity and
5 having a length greater than 8 mm; and
6 a first diode pump source supplying a first pump beam that is
7 incident on a first pump face of the first Nd:YVO₄ gain medium.

1 35. The laser of claim 34, wherein the length of the first
2 Nd:YVO₄ gain medium is greater than 10 mm.

1 36. The laser of claim 34, wherein the length of the first
2 Nd:YVO₄ gain medium is greater than 12 mm.

1 37. The laser of claim 34, wherein the length of the first
2 Nd:YVO₄ gain medium is greater than 16 mm.

1 38. The laser of claim 34, wherein the first Nd:YVO₄ gain
2 medium greater has a pump volume of at least 8 mm³.

1 39. The laser of claim 34, wherein a doping level of the first
2 Nd:YVO₄ gain medium is less than 0.5%.

1 40. The laser of claim 34, wherein the first Nd:YVO₄ gain
2 medium is end-pumped by the first pump beam.

1 41. The laser of claim 34, wherein the first diode pump source is
2 fiber coupled.

1 42. The laser of claim 41, wherein the first diode pump source
2 provides a pump beam with at least 20 watts of power incident on the first
3 pump face of the first Nd:YVO₄ gain medium.

1 43. The laser of claim 34, further comprising:
2 a second diode pump source supplying a second pump beam that is
3 incident on a second pump face of the first Nd:YVO₄ gain medium.

1 44. The laser of claim 43, wherein the first and second diode
2 pump sources are fiber coupled.

1 45. The laser of claim 44, wherein the second diode pump source
2 provides a pump beam with at least 20 watts of power incident on the
3 second pump face of the first Nd:YVO₄ gain medium.

1 46. The laser of claim 43, further comprising:
2 a second Nd:YVO₄ gain medium positioned in the resonator cavity;
3 a third diode pump source supplying a third pump beam that is
4 incident on a first pump face of the second Nd:YVO₄ gain medium; and
5 a fourth diode pump source supplying a fourth pump beam that is
6 incident on a second pump face of the second Nd:YVO₄ gain medium.

1 47. The laser of claim 46, wherein the first, second, third and
2 fourth diode pump sources are fiber coupled.

1 48. The laser of claim 34, wherein the laser produces an output
2 beam with a power of at least 10 watts of at 532 nm.

1 49. The laser of claim 34, wherein the laser produces an output
2 beam with a power of at least 20 watts of at 1064 nm.

1 50. A diode pumped laser, comprising:
2 a first high reflector mirror and an output coupler defining a
3 resonator cavity;
4 a first Nd:YVO₄ gain medium positioned in the resonator cavity
5 with a doping level and a pump volume selected to permit the first
6 Nd:YVO₄ gain medium to be passively cooled; and
7 a first diode pump source supplying a first pump beam that is
8 incident on a first pump face of the first Nd:YVO₄ gain medium, wherein
9 the laser produces an output beam with a power of at least 5 watts at 532
10 nm.

1 51. The laser of claim 50, wherein the output beam has a power
2 of at least 7 watts at 532 nm.

1 52. The laser of claim 50, wherein the pump volume is at least 8
2 mm³.

1 53. The laser of claim 50, wherein a doping level of the first
2 Nd:YVO₄ gain medium is less than 0.5%.

1 54. The laser of claim 50, wherein a length of the first Nd:YVO₄
2 gain medium is greater than 8 mm.

1 55. The laser of claim 50, wherein the first Nd:YVO₄ gain
2 medium is end-pumped by the first pump beam.

1 56. The laser of claim 50, wherein the first diode pump source is
2 fiber coupled.

1 57. The laser of claim 56, wherein the first diode pump source
2 provides a pump beam with at least 20 watts of power incident on the first
3 pump face of the first Nd:YVO₄ gain medium.

1 58. The laser of claim 50, further comprising:
2 a second diode pump source supplying a second pump beam that is
3 incident on a second pump face of the first Nd:YVO₄ gain medium.

1 59. The laser of claim 58, wherein the first and second diode
2 pump sources are fiber coupled.

1 60. The laser of claim 59, wherein the second diode pump source
2 provides a pump beam with at least 20 watts of power incident on the
3 second pump face of the first Nd:YVO₄ gain medium.

1 61. The laser of claim 58, further comprising:
2 a second Nd:YVO₄ gain medium positioned in the resonator cavity;
3 a third diode pump source supplying a third pump beam that is
4 incident on a first pump face of the second Nd:YVO₄ gain medium; and
5 a fourth diode pump source supplying a fourth pump beam that is
6 incident on a second pump face of the second Nd:YVO₄ gain medium.

1 62. The laser of claim 61, wherein the first, second, third and
2 fourth diode pump sources are fiber coupled.

1 63. A diode pumped laser, comprising:
2 a first high reflector mirror and an output coupler defining a
3 resonator cavity;
4 a first Nd:YVO₄ gain medium positioned in the resonator cavity
5 with a doping level and a pump volume selected to permit the first
6 Nd:YVO₄ gain medium to be passively cooled; and
7 a first diode pump source supplying a first pump beam that is
8 incident on a first pump face of the first Nd:YVO₄ gain medium, wherein
9 the laser produces an output beam with a power of at least 10 watts at 1064
10 nm.

1 64. The laser of claim 63, wherein the output beam has a power
2 of at least 15 watts at 1064.

1 65. The laser of claim 63, wherein the output beam has a power
2 of at least 20 watts at 1064.

1 66. The laser of claim 63, wherein the pump volume is at least 8
2 mm³.

1 67. The laser of claim 63, wherein a doping level of the first
2 Nd:YVO₄ gain medium is less than 0.5%.

1 68. The laser of claim 63, wherein a length of the first Nd:YVO₄
2 gain medium is greater than 8 mm.

1 69. The laser of claim 63, wherein the first Nd:YVO₄ gain
2 medium is end-pumped by the first pump beam.

1 70. The laser of claim 63, wherein the first diode pump source is
2 fiber coupled.

1 71. The laser of claim 63, wherein the first diode pump source
2 provides a pump beam with at least 20 watts of power incident on the first
3 pump face of the first Nd:YVO₄ gain medium.

1 72. The laser of claim 63, further comprising:
2 a second diode pump source supplying a second pump beam that is
3 incident on a second pump face of the first Nd:YVO₄ gain medium.

1 73. The laser of claim 72, wherein the first and second diode
2 pump sources are fiber coupled.

1 74. The laser of claim 72, wherein the second diode pump source
2 provides a pump beam with at least 20 watts of power incident on the
3 second pump face of the first Nd:YVO₄ gain medium.

1 75. The laser of claim 72, further comprising:
2 a second Nd:YVO₄ gain medium positioned in the resonator cavity;
3 a third diode pump source supplying a third pump beam that is
4 incident on a first pump face of the second Nd:YVO₄ gain medium; and
5 a fourth diode pump source supplying a fourth pump beam that is
6 incident on a second pump face of the second Nd:YVO₄ gain medium.

1 76. The laser of claim 75, wherein the first, second, third and
2 fourth diode pump sources are fiber coupled.

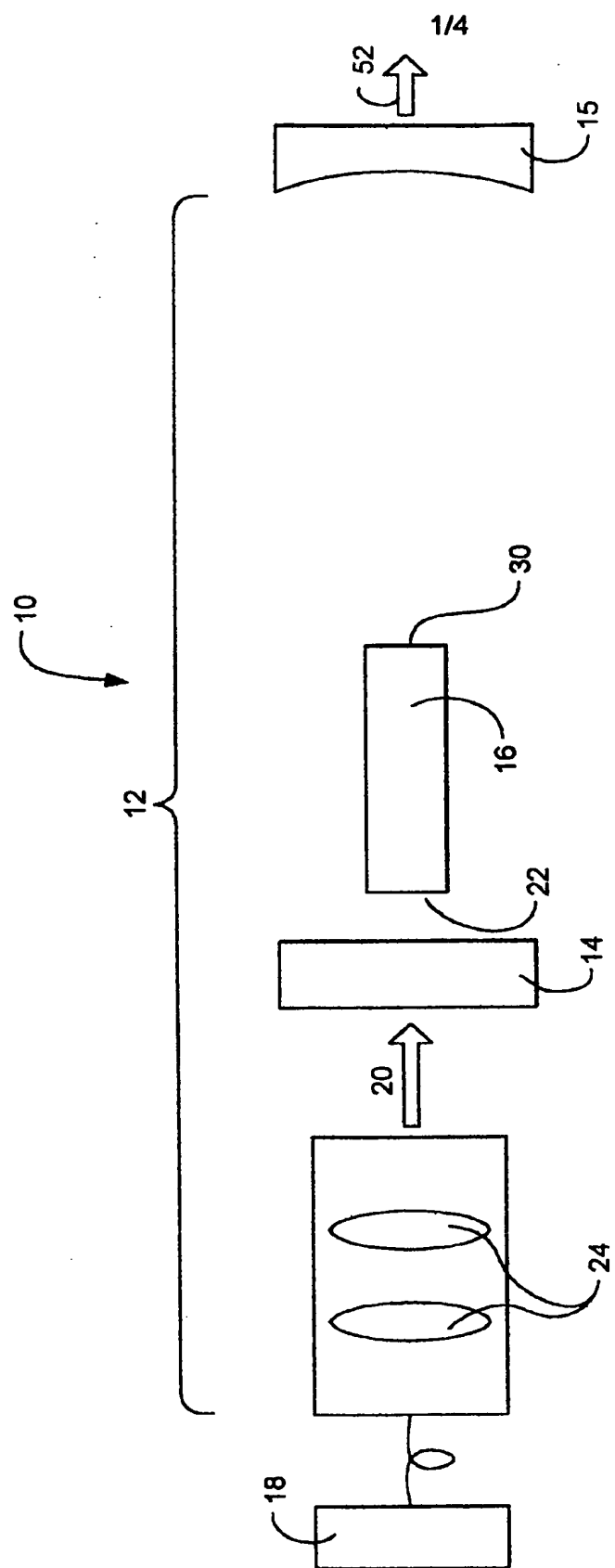


FIG. 1

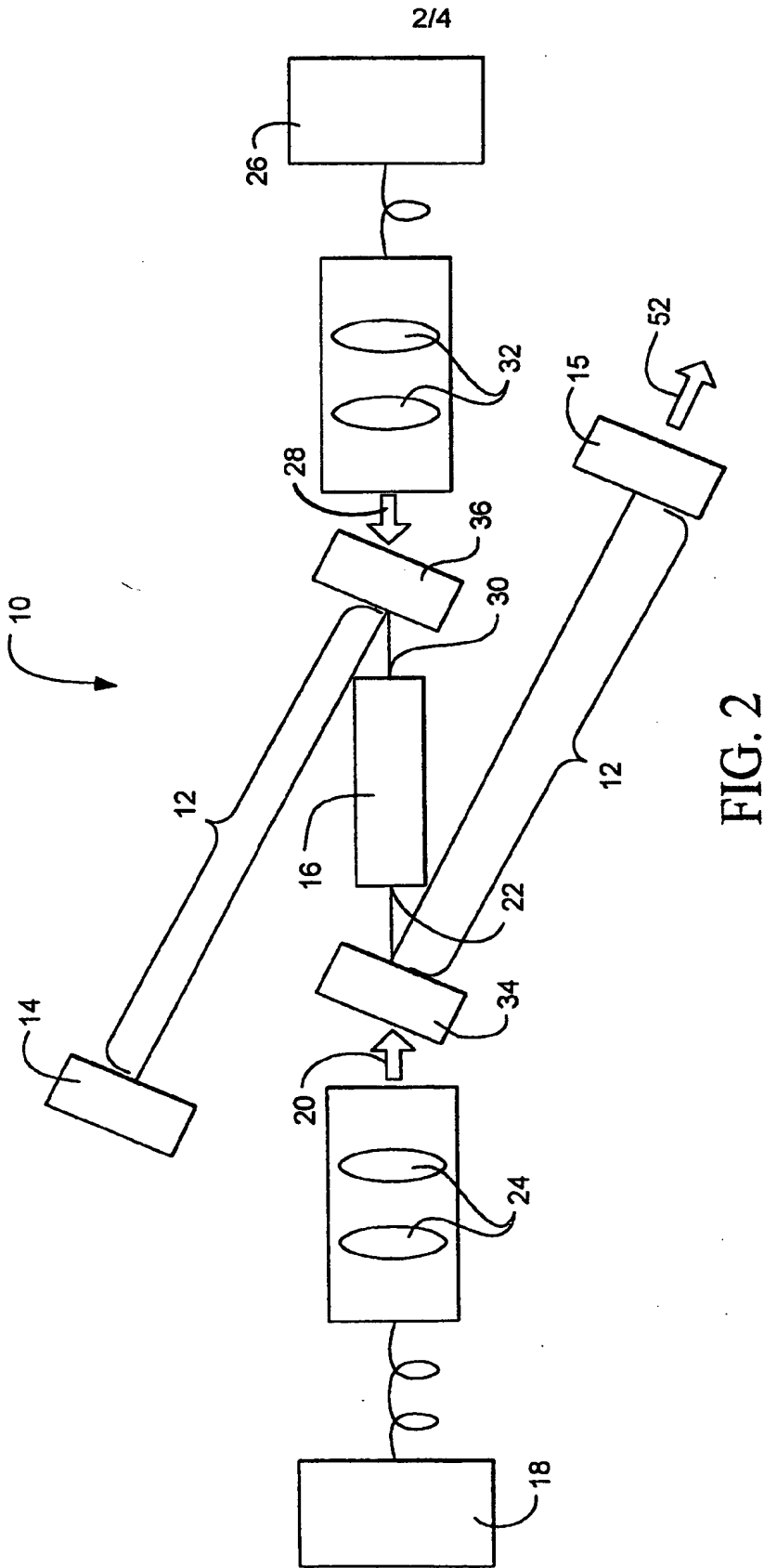
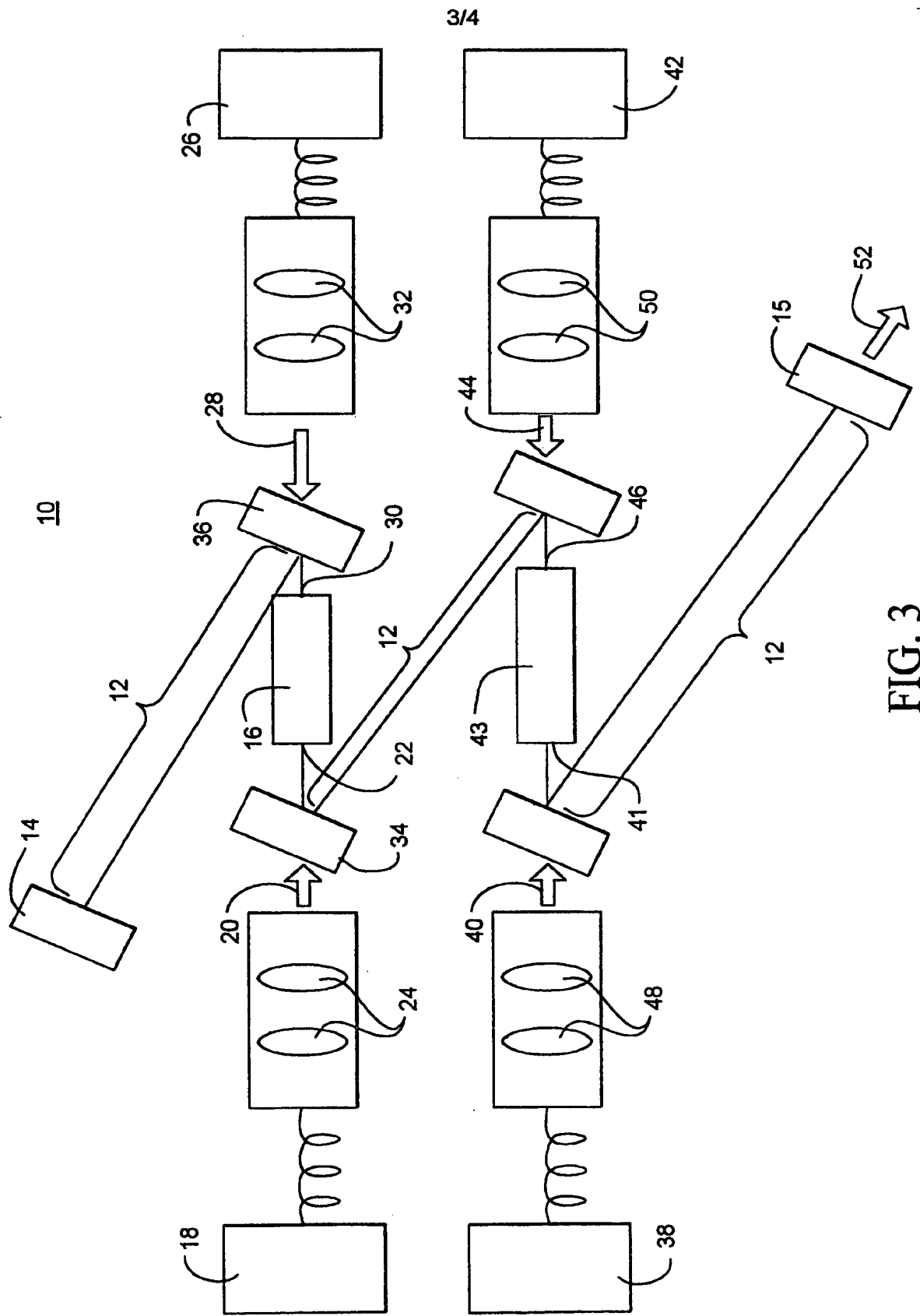


FIG. 2



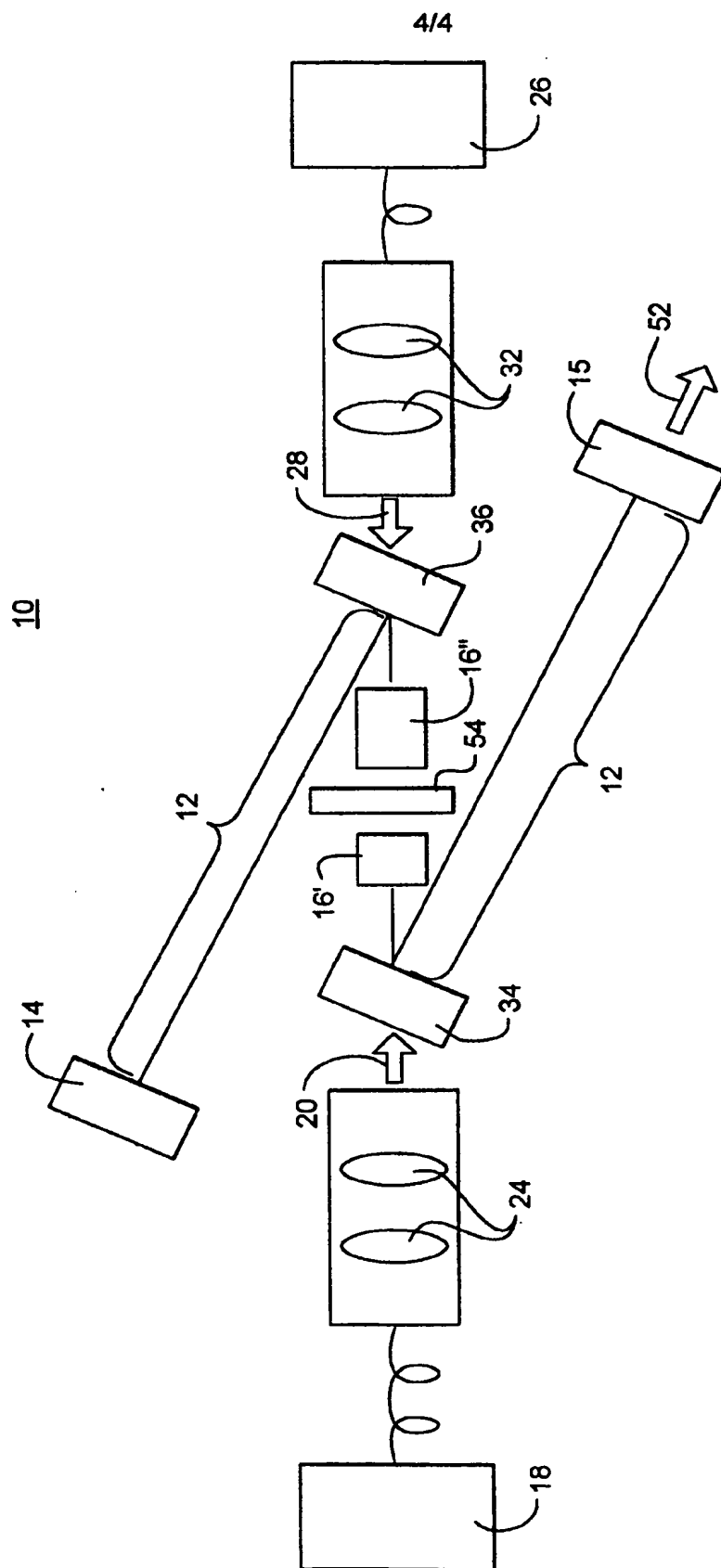


FIG. 4

INTERNATIONAL SEARCH REPORT

Interr. Application No
PCT/US 99/23750

A. CLASSIFICATION OF SUBJECT MATTER IPC 7 H01S3/0941 H01S3/16 H01S3/109		
According to International Patent Classification (IPC) or to both national classification and IPC		
B. FIELDS SEARCHED Minimum documentation searched (classification system followed by classification symbols) IPC 7 H01S		
Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched		
Electronic data base consulted during the international search (name of data base and, where practical, search terms used)		
C. DOCUMENTS CONSIDERED TO BE RELEVANT		
Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 5 410 559 A (NIGHAN JR WILLIAM L ET AL) 25 April 1995 (1995-04-25) column 8, line 32 - line 55 column 9, line 11 - line 43 column 6, line 55 - line 60; figure 3 ---	1-12, 19-26, 29, 33-42, 49,63-71
X	US 5 638 397 A (NIGHAN JR WILLIAM L ET AL) 10 June 1997 (1997-06-10) column 9, line 45 - line 56; figures 7,9 --- -/--	1,13-17, 20, 27-31, 33,34, 43-47, 63,72-76
<div style="display: flex; justify-content: space-between;"> <input checked="" type="checkbox"/> Further documents are listed in the continuation of box C. <input checked="" type="checkbox"/> Patent family members are listed in annex. </div>		
* Special categories of cited documents :		
<div style="display: flex; justify-content: space-between;"> <div style="width: 45%;"> <p>"A" document defining the general state of the art which is not considered to be of particular relevance</p> <p>"E" earlier document but published on or after the international filing date</p> <p>"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)</p> <p>"O" document referring to an oral disclosure, use, exhibition or other means</p> <p>"P" document published prior to the international filing date but later than the priority date claimed</p> </div> <div style="width: 45%;"> <p>"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention</p> <p>"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone</p> <p>"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art.</p> <p>"&" document member of the same patent family</p> </div> </div>		
Date of the actual completion of the international search <div style="text-align: center; font-weight: bold;">8 February 2000</div>		Date of mailing of the international search report <div style="text-align: center; font-weight: bold;">16/02/2000</div>
Name and mailing address of the ISA European Patent Office, P.B. 5818 Patentlaan 2 NL - 2280 HV Rijswijk Tel. (+31-70) 340-2040, Tx. 31 651 epo nl, Fax: (+31-70) 340-3016		Authorized officer <div style="text-align: center; font-weight: bold;">Galanti, M</div>

INTERNATIONAL SEARCH REPORT

Inter. Application No
PCT/US 99/23750

C.(Continuation) DOCUMENTS CONSIDERED TO BE RELEVANT		
Category *	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 5 638 388 A (NIGHAN JR WILLIAM L ET AL) 10 June 1997 (1997-06-10) column 13, line 23 -column 14, line 11 column 5, line 35 - line 38 ----	50-62
A	ZHANG J ET AL: "EFFICIENT TEMOO OPERATION OF ND:YVO4 LASER END PUMPED BY FIBRE-COUPLED DIODE LASER" ELECTRONICS LETTERS,GB,IEE STEVENAGE, vol. 33, no. 9, 24 April 1997 (1997-04-24), pages 775-777, XP000695325 ISSN: 0013-5194 the whole document ----	1,11,12, 63,64
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P,X	WO 99 21250 A (SPECTRA PHYSICS LASERS INC) 29 April 1999 (1999-04-29) abstract -----	1-12, 19-26, 33-42, 63-71

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